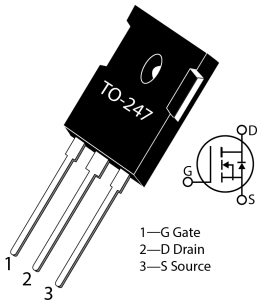
MSC035SMA070B Silicon Carbide N-Channel Power MOSFET

Product Overview

The silicon carbide (SiC) power MOSFET product line from Microsemi increases the performance over silicon MOSFET and silicon IGBT solutions while lowering the total cost of ownership for high-voltage applications. The MSC035SMA070B device is a 700 V, 35 mΩ SiC MOSFET in a TO-247 package.



Features

The following are key features of the MSC035SMA070B device:

- Low capacitances and low gate charge
- Fast switching speed due to low internal gate resistance (ESR)
- Stable operation at high junction temperature, $T_{J(max)}$ = 175 °C
- Fast and reliable body diode
- Superior avalanche ruggedness
- RoHS compliant

Benefits

The following are benefits of the MSC035SMA070B device:

- High efficiency to enable lighter, more compact system
- Simple to drive and easy to parallel
- Improved thermal capabilities and lower switching losses
- Eliminates the need for external freewheeling diode
- Lower system cost of ownership

Applications

The MSC035SMA070B device is designed for the following applications:

- PV inverter, converter, and industrial motor drives
- Smart grid transmission and distribution
- Induction heating and welding
- H/EV powertrain and EV charger
- Power supply and distribution

Device Specifications

This section shows the specifications of the MSC035SMA070B device.

Absolute Maximum Ratings

The following table shows the absolute maximum ratings of the MSC035SMA070B device.

Table 1 • Absolute Maximum Ratings

Symbol	Characteristic	Ratings	Unit
V_{DSS}	Drain source voltage	700	V
I_D	Continuous drain current at T_C = 25 °C	77	A
	Continuous drain current at T_C = 100 °C	54	
I_{DM}	Pulsed drain current[1]	192	
V_{GS}	Gate-source voltage	23 to –10	V
P_D	Total power dissipation at T_C = 25 °C	283	W
	Linear derating factor	1.9	W/°C

Note:

1. Repetitive rating: pulse width and case temperature limited by maximum junction temperature.

The following table shows the thermal and mechanical characteristics of the MSC035SMA070B device.

Table 2 • Thermal and Mechanical Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction-to-case thermal resistance		0.38	0.53	°C/W
T_J	Operating junction temperature	–55		175	°C
T_{STG}	Storage temperature	–55		150	
T_L	Soldering temperature for 10 seconds (1.6 mm from case)			260	
	Mounting torque, 6-32 or M3 screw			10	lbf-in
				1.1	N-m
Wt	Package weight		0.22		oz
			6.2		g

Electrical Performance

The following table shows the static characteristics of the MSC035SMA070B device. T_J = 25 °C unless otherwise specified.

Table 3 • Static Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0 V, I_D = 100 µA	700			V
$R_{DS(on)}$	Drain-source on resistance[1]	V_{GS} = 20 V, I_D = 30 A		35	44	mΩ
$V_{GS(th)}$	Gate-source threshold voltage	V_{GS} = $V_{DS,}$ I_D = 2 mA	1.9	2.7		V
$\Delta V_{GS(th)}/\Delta T_J$	Threshold voltage coefficient	V_{GS} = V_{DS}, I_D = 2 mA		–4.7		mV/°C
I_{DSS}	Zero gate voltage drain current	$V_{DS,}$ = 700 V, V_{GS} = 0 V			100	µA
		V_{DS} = 700 V, V_{GS} = 0 V T_J = 125 °C			500	
I_{GSS}	Gate-source leakage current	V_{GS} = 20 V			100	nA
		V_{GS} = –10 V			100	

Note:

1. Pulse test: pulse width < 380 µs, duty cycle < 2%.

The following table shows the dynamic characteristics of the MSC035SMA070B device. T_J = 25 °C unless otherwise specified.

Table 4 • Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input capacitance	V_{GS} = 0 V, V_{DD} = 700 V, V_{AC} = 25 mV, ƒ = 1 MHz		2010		pF
C_{rss}	Reverse transfer capacitance			17		
C_{oss}	Output capacitance			247		
Q_g	Total gate charge	V_{GS} = –5 V/20 V, V_{DD} = 470 V, I_D = 30 A		99		nC
Q_{gs}	Gate-source charge			33		
Q_{gd}	Gate-drain charge			18		
$t_{d(on)}$	Turn-on delay time	V_{DD} = 470 V, V_{GS} = –5 V/20 V, I_D = 50 A $R_{G(ext)}$ = 4.0 Ω[1], Freewheeling diode = MSC050SDA070B		12		ns
t_r	Current rise time			9		
$t_{d(off)}$	Turn-off delay time			35		

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
t_f	Current fall time			21		
E_{on}	Turn-on switching energy[2]			271		µJ
E_{off}	Turn-off switching energy			57		
$t_{d(on)}$	Turn-on delay time	V_{DD} = 470 V, V_{GS} = -5 V/20 V, I_D = 50 A $R_{G(ext)}$ = 4.0 Ω[1] Freewheeling diode = MSC035SMA070B (V_{GS} = –5 V)		10		ns
t_r	Current rise time			9		
$t_{d(off)}$	Turn-off delay time			40		
t_f	Current fall time			25		
E_{on}	Turn-on switching energy[2]			313		µJ
E_{off}	Turn-off switching energy			55		
ESR	Equivalent series resistance	f = 1 MHz, 25 mV, drain short		1.13		Ω
SCWT	Short circuit withstand time	V_{DS} = 560 V, V_{GS} = 20 V		3		µs
E_{AS}	Avalanche energy, single pulse	V_{DS} = 150 V, V_{GS} = 20 V, I_D = 30 A		1400		mJ

Notes:

1. R_G is total gate resistance excluding internal gate driver impedance.
2. E_{on} includes energy of freewheeling diode.

The following table shows the body diode characteristics of the MSC035SMA070B device.

Table 5 • Body Diode Characteristics

Sym-bol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{SD}	Diode forward voltage	I_{SD} = 30 A, V_{GS} = 0 V		3.8		V
		I_{SD} = 30 A, V_{GS} = –5 V		4.0		V
t_{rr}	Reverse recovery time	I_{SD} = 30 A, V_{GS} = –5 V V_{DD} = 470 V dI/dt = –1000 A/µs		75		ns
Q_{rr}	Reverse recovery charge			305		nC
I_{RRM}	Reverse recovery current			11		A

Typical Performance Curves

This section shows the typical performance curves of the MSC035SMA070B device.

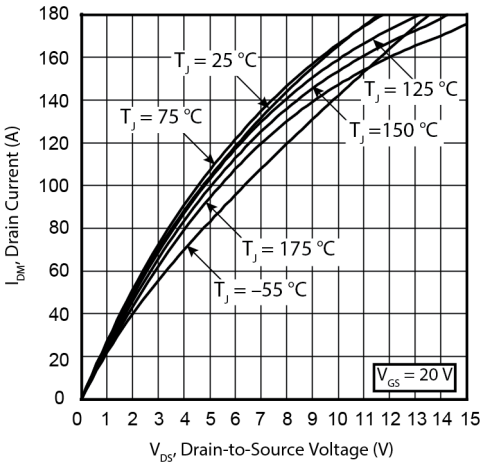


Figure 1 • Drain Current vs. V_{DS}

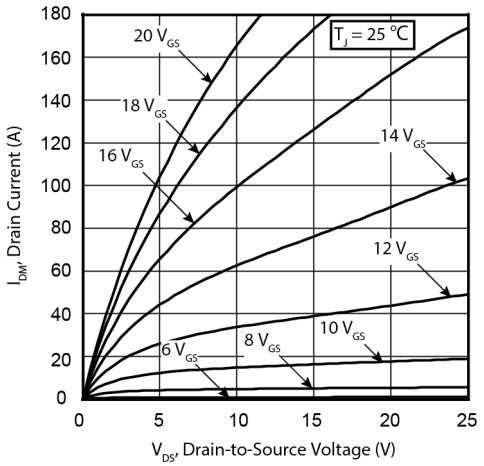


Figure 2 • Drain Current vs. V_{DS}

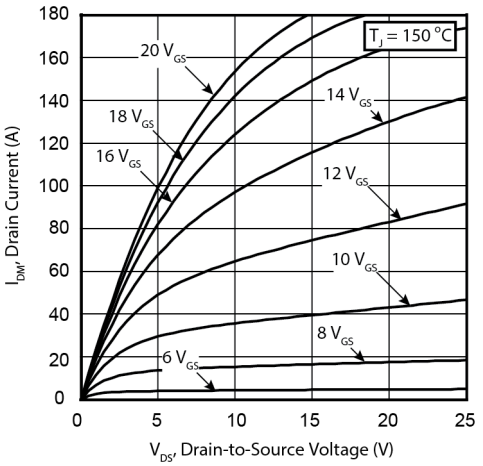


Figure 3 • Drain Current vs. V_{DS}

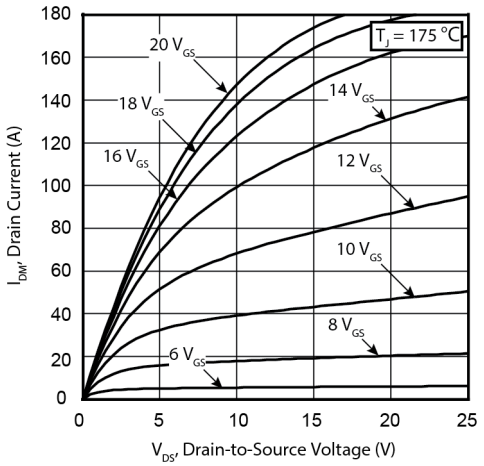


Figure 4 • Drain Current vs. V_{DS}

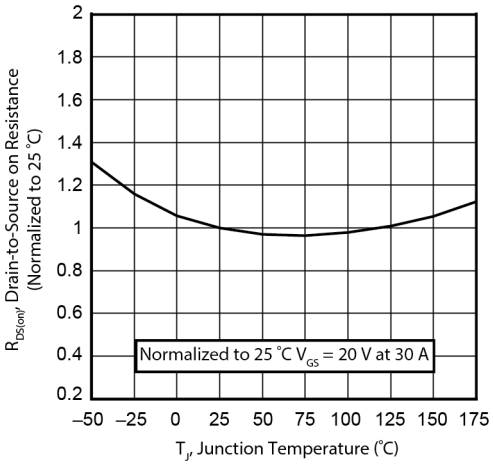


Figure 5 • RDS(on) vs. Junction Temperature

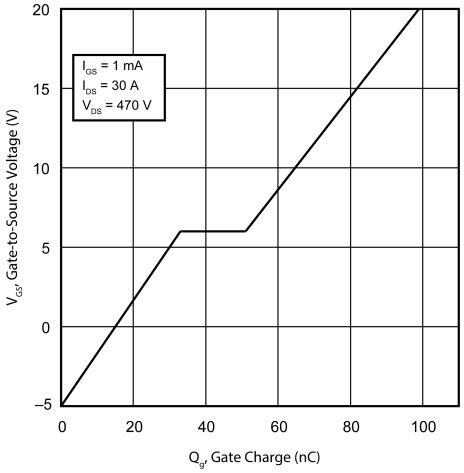


Figure 6 • Gate Charge Characteristics

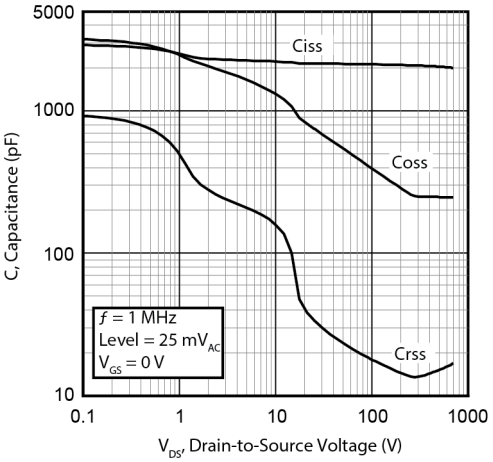


Figure 7 • Capacitance vs. V_{DS}

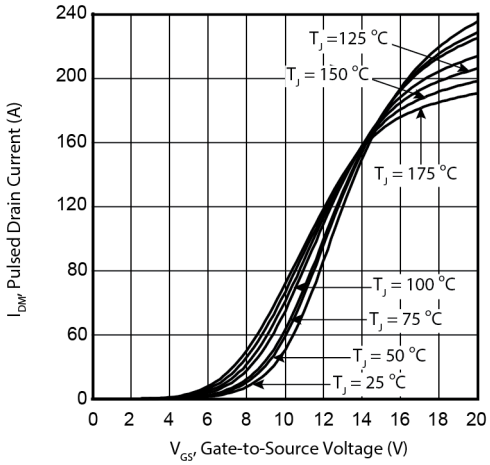


Figure 8 • I_{DM} vs. V_{GS}

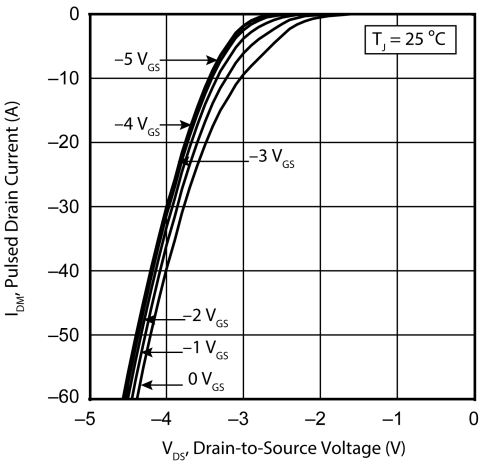


Figure 9 • I_{DM} vs. V_{DS} 3rd Quadrant Condition

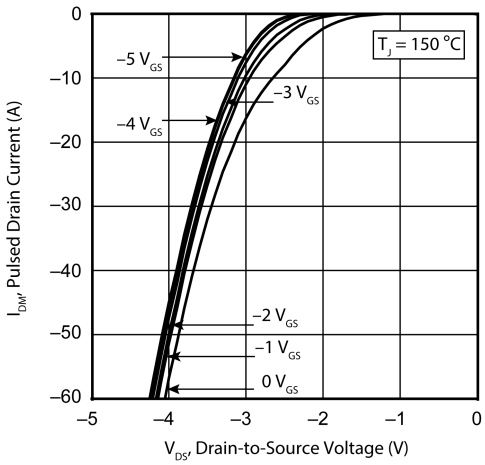


Figure 10 • I_{DM} vs. V_{DS} 3rd Quadrant Condition

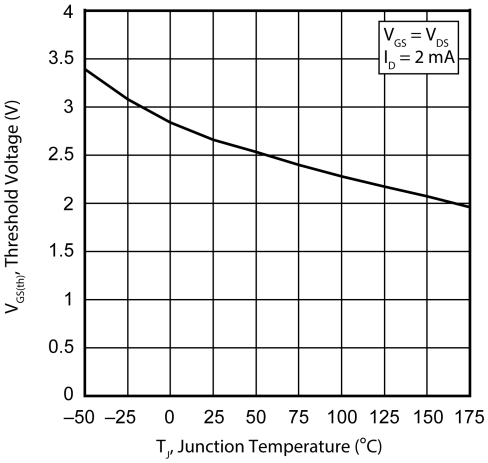


Figure 11 • $V_{GS(th)}$ vs. Junction Temperature

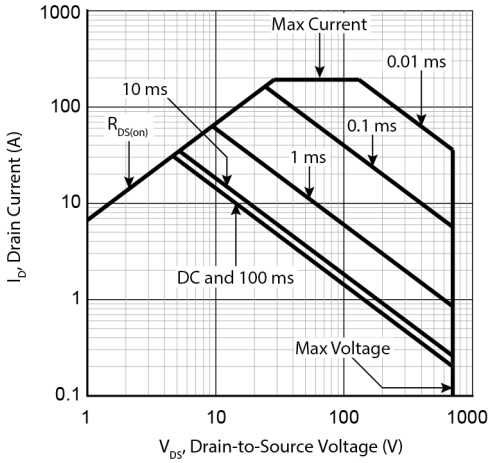


Figure 12 • Forward Safe Operating Area

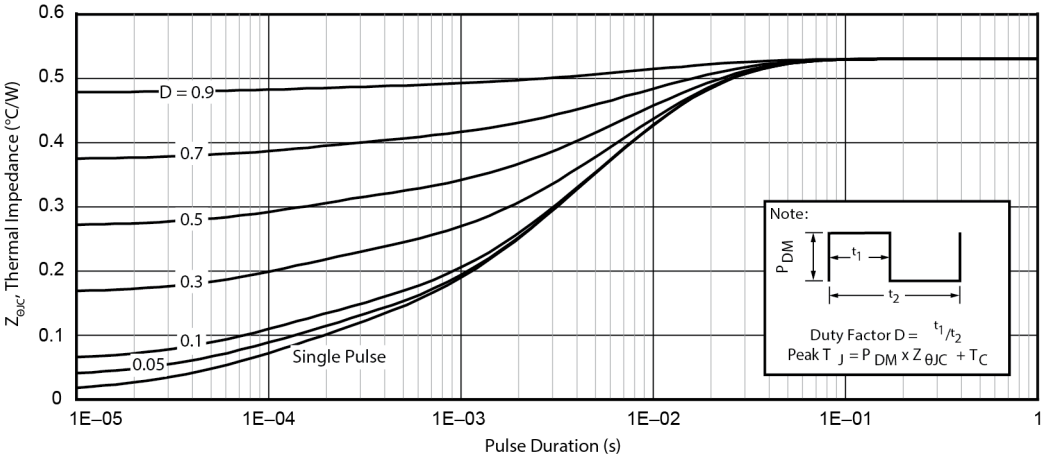


Figure 13 • Maximum Transient Thermal Impedance

Package Specification

This section shows the package specification of the MSC035SMA070B device.

Package Outline Drawing

This section shows the TO-247 package outline of the MSC035SMA070B device. The dimensions in the figure below are in millimeters and (inches).

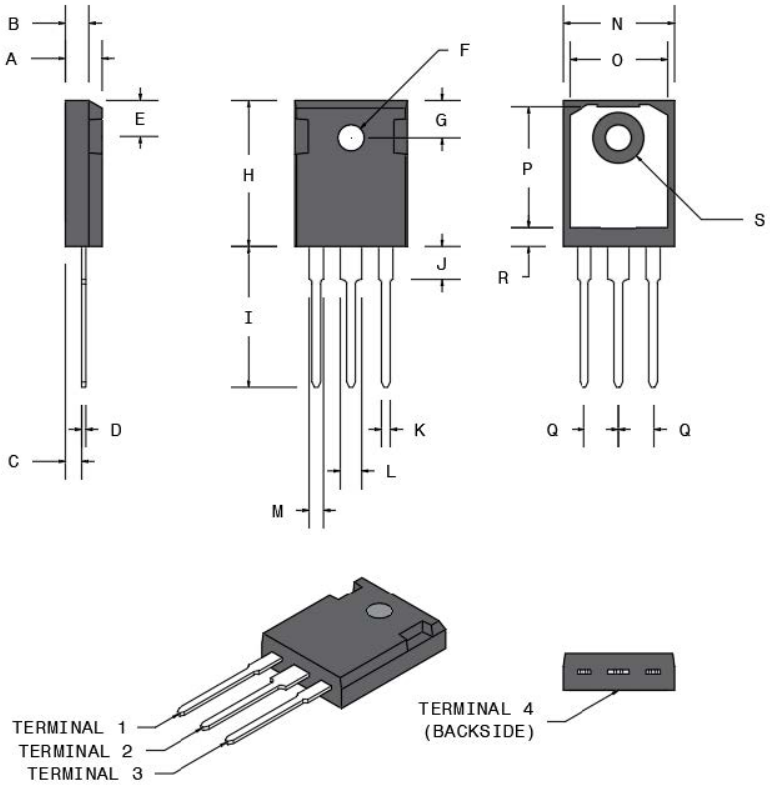


Figure 14 • Package Outline Drawing

The following table shows the MSC080SMA120B dimensions and should be used in conjunction with the package outline drawing.

Table 6 • TO-247 Dimensions

Symbol	Min (mm)	Max (mm)	Min (in.)	Max (in.)
A	4.69	5.31	0.185	0.209
B	1.49	2.49	0.059	0.098
C	2.21	2.59	0.087	0.102
D	0.40	0.79	0.016	0.031
E	5.38	6.20	0.212	0.244

Symbol	Min (mm)	Max (mm)	Min (in.)	Max (in.)
F	3.50	3.81	0.138	0.150
G	6.15 BSC		0.242 BSC	
H	20.80	21.46	0.819	0.845
I	19.81	20.32	0.780	0.800
J	4.00	4.50	0.157	0.177
K	1.01	1.40	0.040	0.055
L	2.87	3.12	0.113	0.123
M	1.65	2.13	0.065	0.084
N	15.49	16.26	0.610	0.640
O	13.50	14.50	0.531	0.571
P	16.50	17.50	0.650	0.689
Q	5.45 BSC		0.215 BSC	
R	2.00	2.75	0.079	0.108
S	7.10	7.50	0.280	0.295
Terminal 1	Gate			
Terminal 2	Drain			
Terminal 3	Source			
Terminal 4	Drain			

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